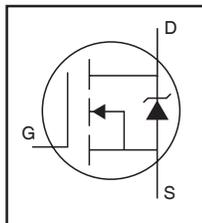


**AUTOMOTIVE GRADE**

**AUIRF2907Z**  
HEXFET® Power MOSFET

**Features**

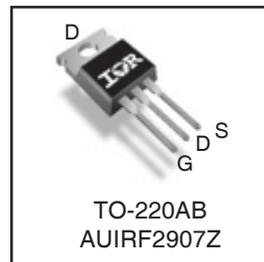
- Advanced Process Technology
- Ultra Low On-Resistance
- 175°C Operating Temperature
- Fast Switching
- Repetitive Avalanche Allowed up to Tjmax
- Lead-Free, RoHS Compliant
- Automotive Qualified \*



$V_{(BR)DSS}$	<b>75V</b>
$R_{DS(on)}$ max.	<b>4.5mΩ</b>
$I_D$ (Silicon Limited)	<b>170A</b>
$I_D$ (Package Limited)	<b>75A</b>

**Description**

Specifically designed for Automotive applications, this HEXFET® Power MOSFET utilizes the latest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of this design are a 175°C junction operating temperature, fast switching speed and improved repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in Automotive applications and a wide variety of other applications.



<b>G</b>	<b>D</b>	<b>S</b>
Gate	Drain	Source

**Absolute Maximum Ratings**

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature ( $T_A$ ) is 25°C, unless otherwise specified.

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$ (Silicon Limited)	170	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$ (Silicon Limited)	120	
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$ (Package Limited)	75	
$I_{DM}$	Pulsed Drain Current ①	680	
$P_D @ T_C = 25^\circ\text{C}$	Maximum Power Dissipation	300	W
	Linear Derating Factor	2.0	W/°C
$V_{GS}$	Gate-to-Source Voltage	± 20	V
$E_{AS}$	Single Pulse Avalanche Energy (Thermally Limited) ②	270	mJ
$E_{AS}$ (tested)	Single Pulse Avalanche Energy Tested Value ②	690	
$I_{AR}$	Avalanche Current ①	See Fig.12a,12b,15,16	A
$E_{AR}$	Repetitive Avalanche Energy ③		mJ
$T_J$	Operating Junction and	-55 to + 175	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 seconds (1.6mm from case )		
	Mounting torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

**Thermal Resistance**

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ③	—	0.50④	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient	—	62	

HEXFET® is a registered trademark of International Rectifier.

\*Qualification standards can be found at <http://www.irf.com/>

### Static Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	75	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.069	—	V/°C	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	3.5	4.5	mΩ	$V_{GS} = 10V, I_D = 75A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
gfs	Forward Transconductance	180	—	—	S	$V_{DS} = 25V, I_D = 75A$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	20	μA	$V_{DS} = 75V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 75V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	200	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-200		$V_{GS} = -20V$

### Dynamic Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$Q_g$	Total Gate Charge	—	180	270	nC	$I_D = 75A$ $V_{DS} = 60V$ $V_{GS} = 10V$ ④
$Q_{gs}$	Gate-to-Source Charge	—	46	—		
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	65	—		
$t_{d(on)}$	Turn-On Delay Time	—	19	—	ns	$V_{DD} = 38V$ $I_D = 75A$ $R_G = 2.5\Omega$ $V_{GS} = 10V$ ④
$t_r$	Rise Time	—	140	—		
$t_{d(off)}$	Turn-Off Delay Time	—	97	—		
$t_f$	Fall Time	—	100	—		
$L_D$	Internal Drain Inductance	—	5.0	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
$L_S$	Internal Source Inductance	—	13	—		
$C_{iss}$	Input Capacitance	—	7500	—	pF	$V_{GS} = 0V$
$C_{oss}$	Output Capacitance	—	970	—		$V_{DS} = 25V$
$C_{rss}$	Reverse Transfer Capacitance	—	510	—		$f = 1.0\text{MHz}$ , See Fig. 5
$C_{oss}$	Output Capacitance	—	3640	—		$V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0\text{MHz}$
$C_{oss}$	Output Capacitance	—	650	—		$V_{GS} = 0V, V_{DS} = 60V, f = 1.0\text{MHz}$
$C_{oss\text{ eff.}}$	Effective Output Capacitance	—	1020	—		$V_{GS} = 0V, V_{DS} = 0V \text{ to } 60V$

### Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	75	A	MOSFET symbol showing the integral reverse p-n junction diode.
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	680		
$V_{SD}$	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 75A, V_{GS} = 0V$ ④
$t_{rr}$	Reverse Recovery Time	—	41	61	ns	$T_J = 25^\circ\text{C}, I_F = 75A, V_{DD} = 38V$
$Q_{rr}$	Reverse Recovery Charge	—	59	89	nC	$di/dt = 100A/\mu s$ ④
$t_{on}$	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S+L_D$ )				

#### Notes:

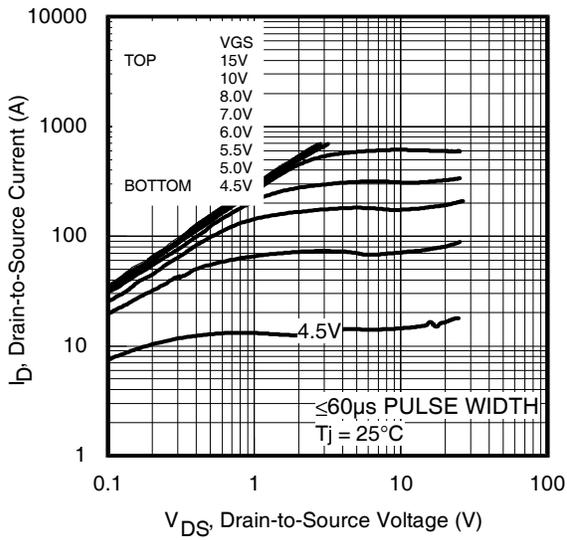
- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11).
- ② Limited by  $T_{Jmax}$ , starting  $T_J = 25^\circ\text{C}, L=0.095\text{mH}, R_G = 25\Omega, I_{AS} = 75A, V_{GS} = 10V$ . Part not recommended for use above this value.
- ③  $I_{SD} \leq 75A, di/dt \leq 340A/\mu s, V_{DD} \leq V_{(BR)DSS}, T_J \leq 175^\circ\text{C}$ .
- ④ Pulse width  $\leq 1.0\text{ms}$ ; duty cycle  $\leq 2\%$ .
- ⑤  $C_{oss\text{ eff.}}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .
- ⑥ Limited by  $T_{Jmax}$ , see Fig.12a, 12b, 15, 16 for typical repetitive avalanche performance.
- ⑦ This value determined from sample failure population, starting  $T_J = 25^\circ\text{C}, L=0.095\text{mH}, R_G = 25\Omega, I_{AS} = 75A, V_{GS} = 10V$ .
- ⑧  $R_\theta$  is measured at  $T_J$  of approximately  $90^\circ\text{C}$ .
- ⑨ TO-220 device will have an  $R_{th}$  of  $0.45^\circ\text{C/W}$ .

## Qualification Information<sup>†</sup>

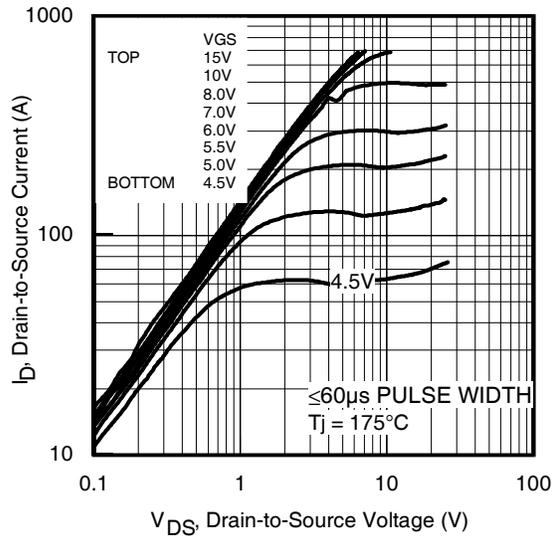
<b>Qualification Level</b>		Automotive (per AEC-Q101) <sup>††</sup>	
		Comments: This part number(s) passed Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
<b>Moisture Sensitivity Level</b>		TO-220AB	N/A
<b>ESD</b>	Machine Model	Class M4 (425V) AEC-Q101-002	
	Human Body Model	Class H2 (4000V) AEC-Q101-001	
	Charged Device Model	Class C4 (1000V) AEC-Q101-005	
<b>RoHS Compliant</b>		Yes	

<sup>†</sup> Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/>

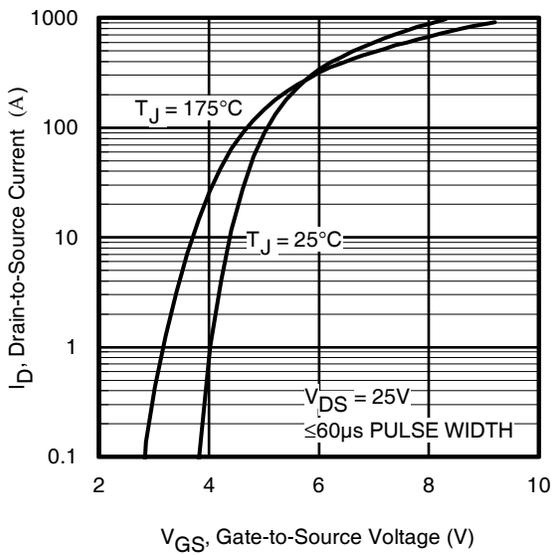
<sup>††</sup> Exceptions to AEC-Q101 requirements are noted in the qualification report.



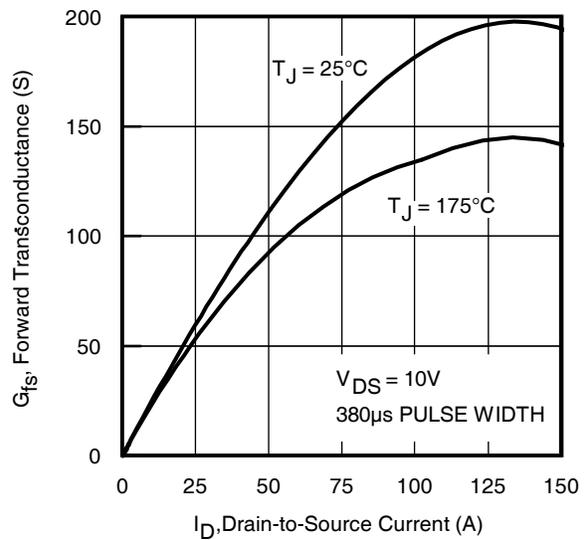
**Fig 1.** Typical Output Characteristics



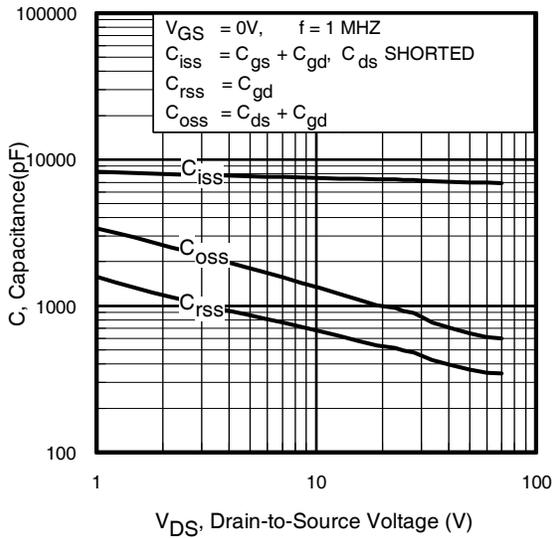
**Fig 2.** Typical Output Characteristics



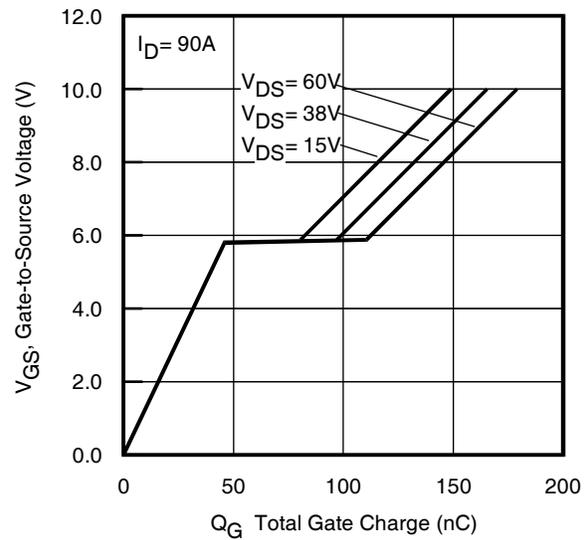
**Fig 3.** Typical Transfer Characteristics



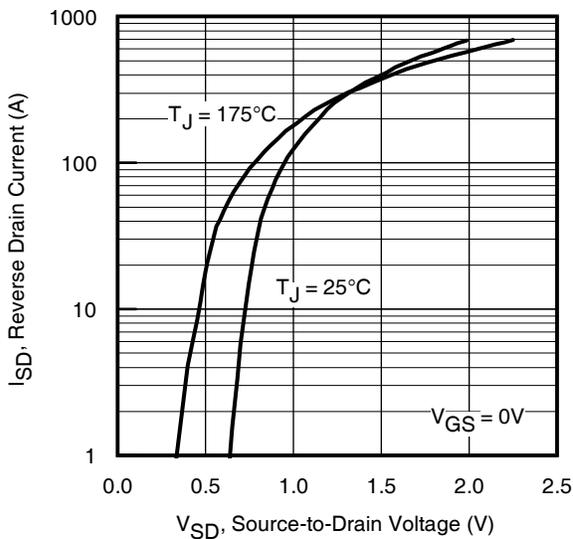
**Fig 4.** Typical Forward Transconductance vs. Drain Current



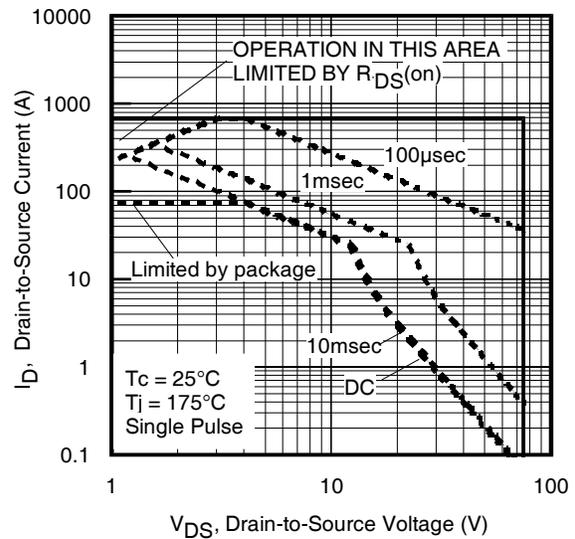
**Fig 5.** Typical Capacitance vs. Drain-to-Source Voltage



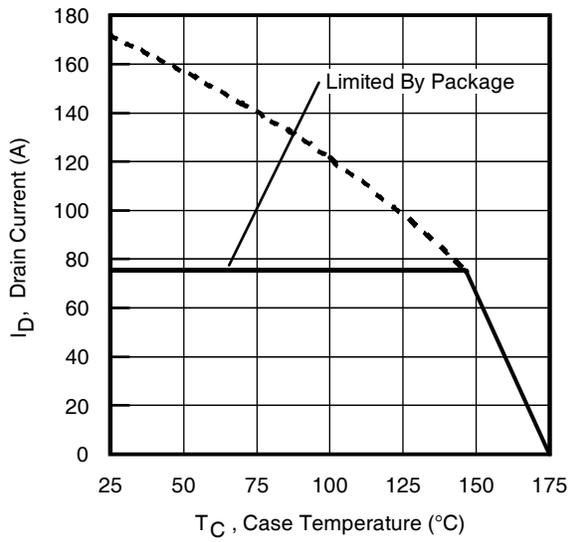
**Fig 6.** Typical Gate Charge vs. Gate-to-Source Voltage



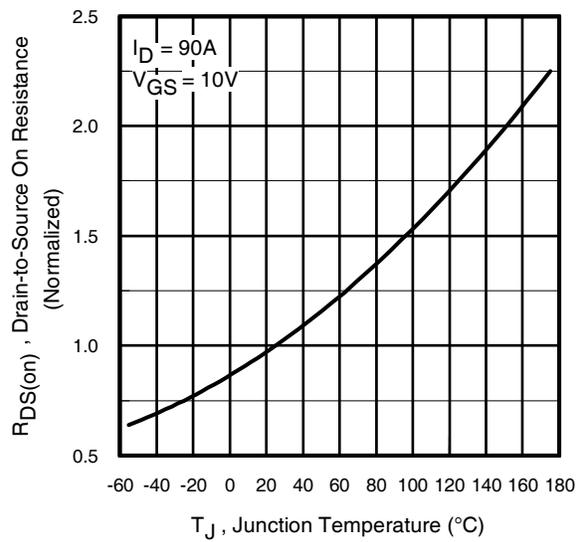
**Fig 7.** Typical Source-Drain Diode Forward Voltage



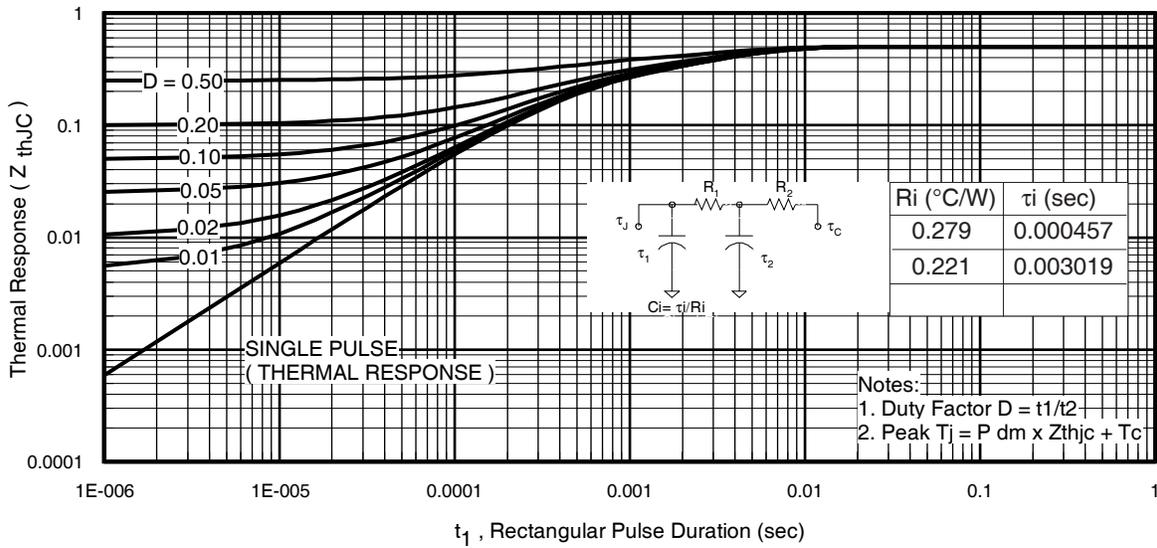
**Fig 8.** Maximum Safe Operating Area



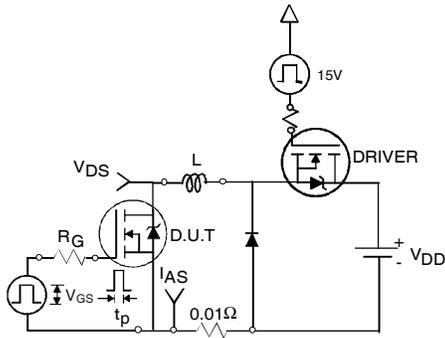
**Fig 9.** Maximum Drain Current vs. Case Temperature



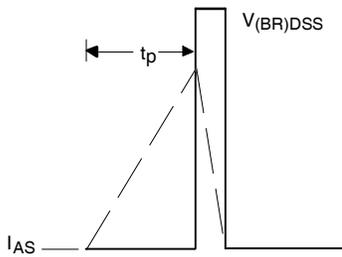
**Fig 10.** Normalized On-Resistance vs. Temperature



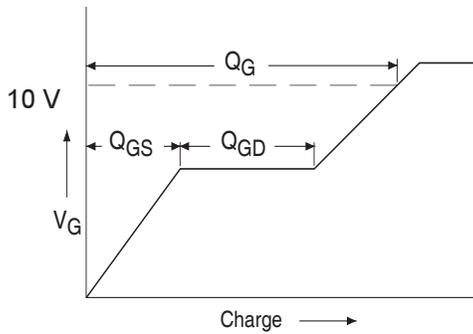
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case



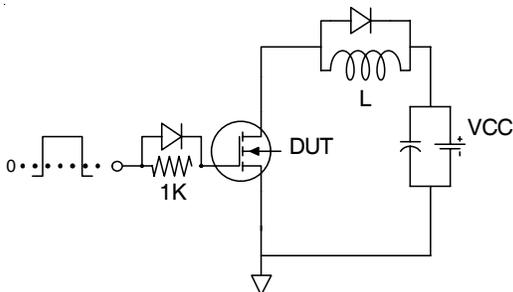
**Fig 12a.** Unclamped Inductive Test Circuit



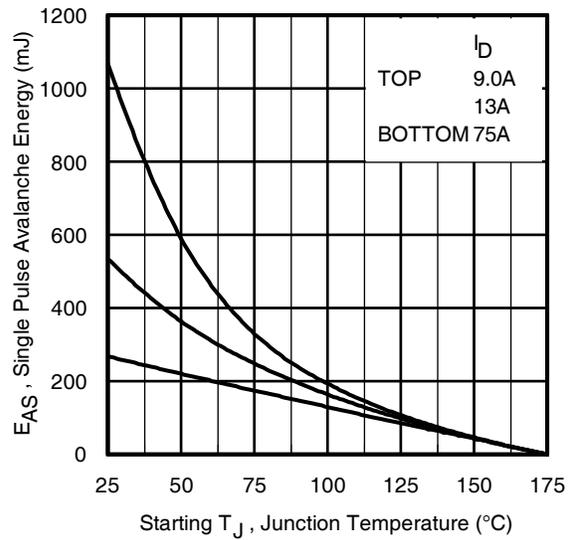
**Fig 12b.** Unclamped Inductive Waveforms



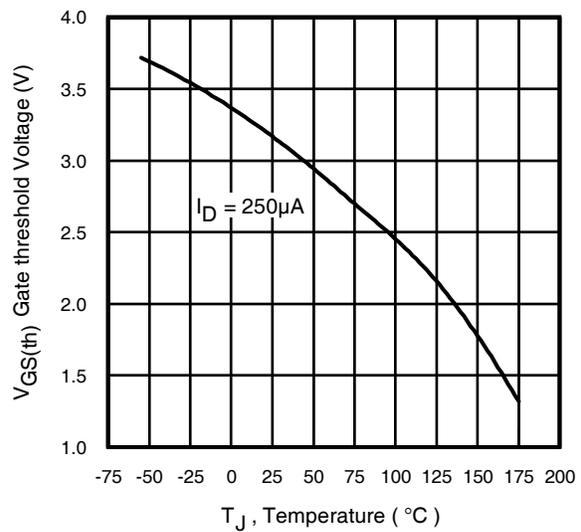
**Fig 13a.** Basic Gate Charge Waveform



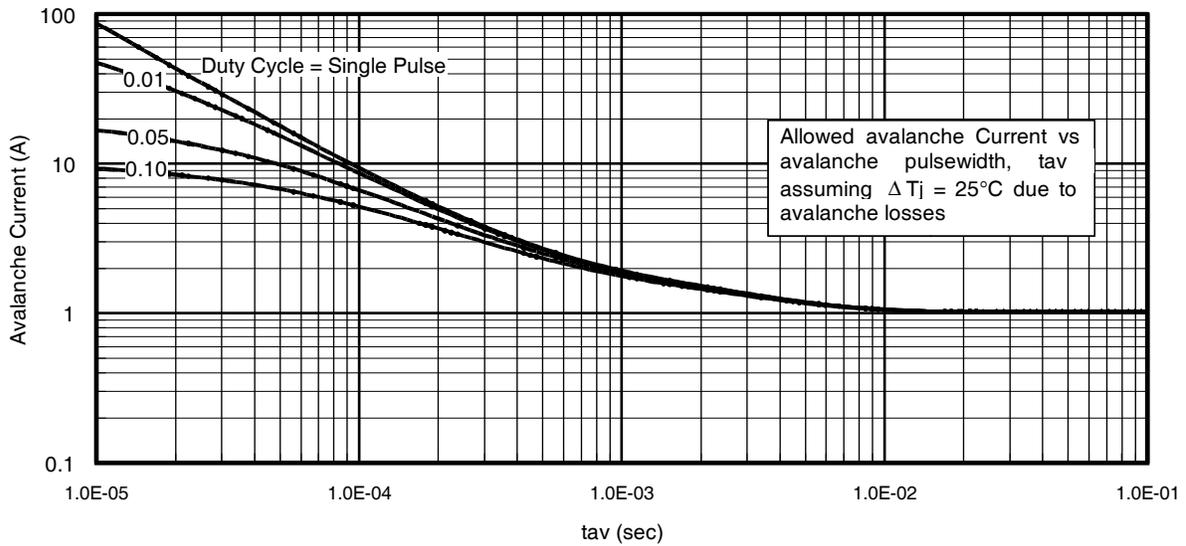
**Fig 13b.** Gate Charge Test Circuit  
www.irf.com



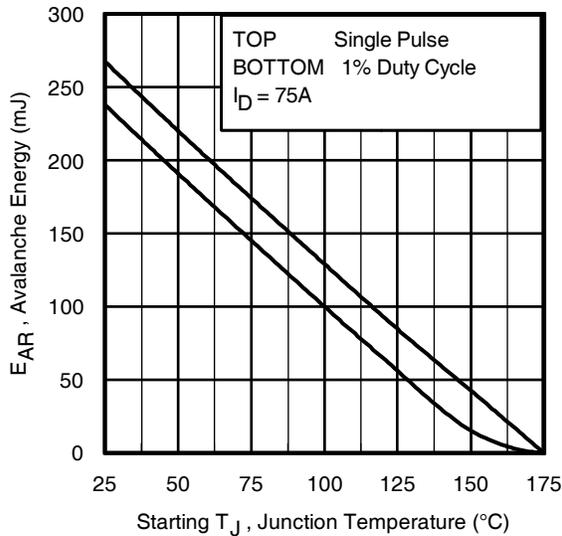
**Fig 12c.** Maximum Avalanche Energy vs. Drain Current



**Fig 14.** Threshold Voltage vs. Temperature



**Fig 15.** Typical Avalanche Current Vs.Pulsewidth



**Notes on Repetitive Avalanche Curves , Figures 15, 16:**  
(For further info, see AN-1005 at [www.irf.com](http://www.irf.com))

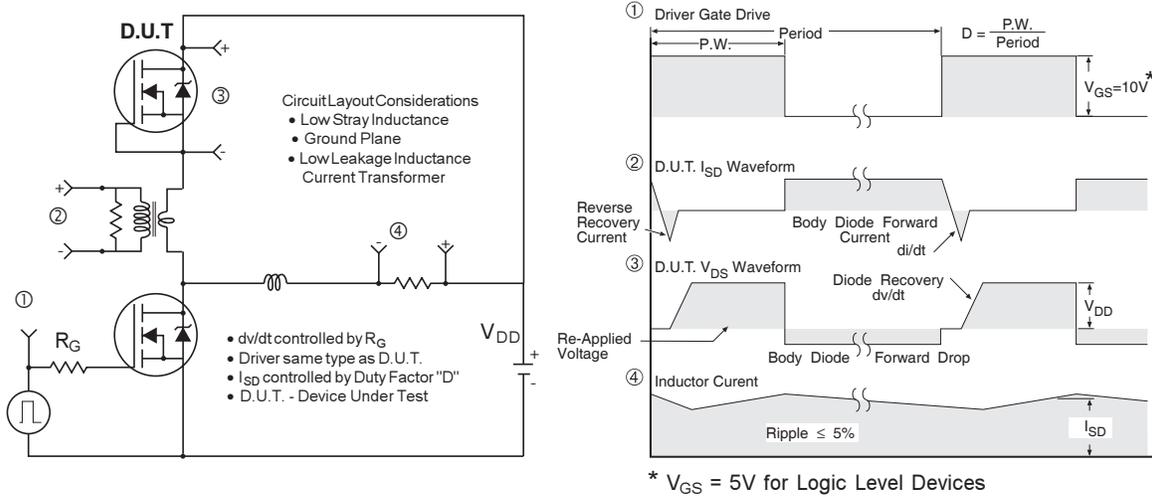
1. Avalanche failures assumption:  
Purely a thermal phenomenon and failure occurs at a temperature far in excess of  $T_{jmax}$ . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as  $T_{jmax}$  is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 12a, 12b.
4.  $P_{D(ave)}$  = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6.  $I_{av}$  = Allowable avalanche current.
7.  $\Delta T$  = Allowable rise in junction temperature, not to exceed  $T_{jmax}$  (assumed as 25°C in Figure 15, 16).  
 $t_{av}$  = Average time in avalanche.  
 $D$  = Duty cycle in avalanche =  $t_{av} \cdot f$   
 $Z_{thJC}(D, t_{av})$  = Transient thermal resistance, see figure 11)

$$P_{D(ave)} = 1/2 ( 1.3 \cdot BV \cdot I_{av} ) = \Delta T / Z_{thJC}$$

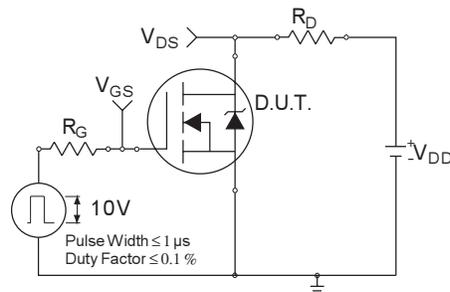
$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$$

$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$

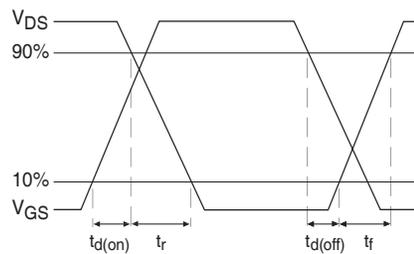
**Fig 16.** Maximum Avalanche Energy vs. Temperature



**Fig 17.** Peak Diode Recovery  $dv/dt$  Test Circuit for N-Channel HEXFET® Power MOSFETs



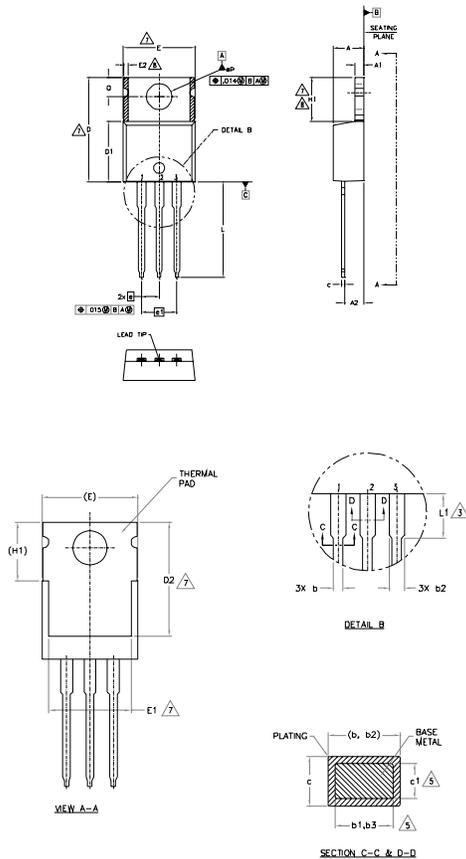
**Fig 18a.** Switching Time Test Circuit



**Fig 18b.** Switching Time Waveforms

## TO-220AB Package Outline

Dimensions are shown in millimeters (inches)

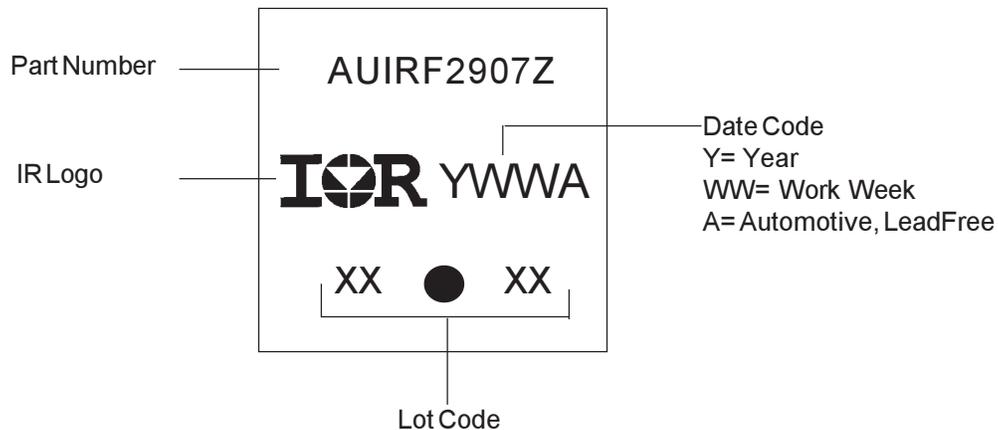


- NOTES:
- 1.- DIMENSIONING AND TOLERANCING AS PER ASME Y14.5 M- 1994.
  - 2.- DIMENSIONS ARE SHOWN IN INCHES (MILLIMETERS).
  - 3.- LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
  - 4.- DIMENSION D, D1 & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
  - 5.- DIMENSION b1, b3 & c1 APPLY TO BASE METAL ONLY.
  - 6.- CONTROLLING DIMENSION ± INCHES.
  - 7.- THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS E1, D2 & E1
  - 8.- DIMENSION E2 X H1 DEFINE A ZONE WHERE STAMPING AND SINGULATION IRREGULARITIES ARE ALLOWED.
  - 9.- OUTLINE CONFORMS TO JEDEC TO-220, EXCEPT A2 (max.) AND D2 (min.) WHERE DIMENSIONS ARE DERIVED FROM THE ACTUAL PACKAGE OUTLINE.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	3.56	4.83	.140	.190	
A1	0.51	1.40	.020	.055	
A2	2.03	2.92	.080	.115	
b	0.38	1.01	.015	.040	
b1	0.38	0.97	.015	.038	5
b2	1.14	1.78	.045	.070	
b3	1.14	1.73	.045	.068	5
c	0.36	0.61	.014	.024	
c1	0.36	0.56	.014	.022	5
D	14.22	16.51	.560	.650	4
D1	8.38	9.02	.330	.355	
D2	11.68	12.88	.460	.507	7
E	9.65	10.67	.380	.420	4,7
E1	6.86	8.89	.270	.350	7
E2	-	0.76	-	.030	8
e	2.54 BSC	-	.100 BSC	-	
e1	3.08 BSC	-	.200 BSC	-	
H1	5.84	6.86	.230	.270	7,8
L	12.70	14.73	.500	.580	
L1	3.56	4.06	.140	.160	3
ØP	3.54	4.08	.139	.161	
Q	2.54	3.42	.100	.135	

- LEAD ASSIGNMENTS
- HEXLET
- 1- GATE
  - 2- GRAB
  - 3- SOURCE
- GEOL. GP. MARKS
- 1- GATE
  - 2- COLLECTOR
  - 3- EMITTER
- DIODES
- 1- ANODE
  - 2- CATHODE
  - 3- ANODE

## TO-220AB Part Marking Information



TO-220AB packages are not recommended for Surface Mount Application.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

## Ordering Information

Base part	Package Type	Standard Pack		Complete Part Number
		Form	Quantity	
AUIRF2907Z	TO-220	Tube	50	AUIRF2907Z

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For technical support, please contact IR's Technical Assistance Center

<http://www.irf.com/technical-info/>

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Tel: (310) 252-7105